In the Claims:

A3

1. (Currently Amended) An in-plane switching mode LCD device comprising:

first and second substrates;

data and gate lines on the first substrate to define a plurality of pixel regions;

at least one data electrode on the first substrate;

at least one common electrode on the first substrate;

a transparent conductive film in a layer over the data electrode, the transparent conductive film electrically connected with the common electrode; and

a liquid crystal layer between the first and second substrates.

2. (Original) The device of claim 1, wherein the transparent conductive film includes indium tin oxide (ITO).

3. (Original) The device of claim 1, further comprising a gate insulating film on the common electrode.

4. (Original) The device of claim 1, further comprising a passivation film on the common electrode.

5. (Original) The device of claim 4, wherein the common electrode is electrically connected with the transparent conductive film through a contact hole in the passivation film.

6. (Original) The device of claim 1, wherein the common electrode is electrically connected with the transparent conductive film through a laser welding.

7. (Original) The device of claim 1, wherein the liquid crystal layer includes a cyano (CN) based liquid crystal.

8. (Original) The device of claim 1, wherein the liquid crystal layer includes a fluorine (F) based liquid crystal.

9. (Original) The device of claim 1, wherein the transparent conductive film is formed outermost to the common electrode.

10. (Original) The device of claim 1, wherein the transparent conductive film extends toward the data electrode.

A4

11. (Currently Amended) A method for manufacturing an in-plane switching mode LCD device comprising:

providing first and second substrates;

forming a plurality of gate lines and common electrodes on the first substrate;

forming a gate insulating film on the common electrodes;

forming a plurality of data lines and data electrodes on the gate insulating film;

forming a transparent conductive film in a layer over the data electrode, the transparent conductive film electrically connected with the common electrodes; and

forming a liquid crystal layer between the first and second substrates.

12. (Original) The method of claim 11, wherein the common electrode is selected from the group of consisting of Al, Cr, Ti and Al alloy.

13. (Original) The method of claim 11, further comprising the step of forming a passivation film on the data electrodes.

14. (Original) The method of claim 11, wherein the common electrode is electrically connected with the transparent conductive film through a contact hole of the passivation film.

15. (Original) The method of claim 11, further comprising the step of electrically connecting the common electrodes with the transparent conductive film.

16. (Original) The method of claim 15, wherein the common electrode is electrically connected with the transparent conductive film through a laser welding.

17. (Original) The method of claim 11, wherein the transparent conductive film includes indium tin oxide (ITO).

18. (Original) The method of claim 11, wherein the liquid crystal layer includes a cyano (CN) based liquid crystal.

19. (Original) The method of claim 11, wherein the liquid crystal layer includes a fluorine (F) based liquid crystal.

20. (Original) The method of claim 11, wherein the transparent conductive film is formed outmost to the common electrodes.

21. (Original) The method of claim 11, wherein the transparent conductive film extends toward at least one of the data electrodes.